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United States Patent Application Publication

20250267917

Kind Code

A1

Publication Date

August 21, 2025

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RING TRANSISTOR STRUCTURE

Abstract

The present disclosure relates to a method. The method includes forming a plurality of first source/drain contacts and a second source/drain contact over a substrate. The second source/drain contact wraps around the plurality of first source/drain contacts. A plurality of gate structures are over the substrate. The plurality of gate structures are laterally between the plurality of first source/drain contacts and the second source/drain contact. An isolation region is formed within the substrate. The isolation region has one or more curved edges that face a curved outermost sidewall of the second source/drain contact. The one or more curved edges are separated from the curved outermost sidewall by a non-zero distance.

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Family ID: 1000008575168

Appl. No.: 19/199629

Filed: May 06, 2025

Related U.S. Application Data

parent US continuation 18302174 20230418 parent-grant-document US 12324211 child US 19199629

parent US continuation 17144671 20210108 parent-grant-document US 11664431 child US 18302174

Publication Classification

Int. Cl.: H10D64/23 (20250101); **H10D30/47** (20250101); **H10D64/00** (20250101); **H10D64/01** (20250101); **H10D64/27** (20250101)

U.S. Cl.:

CPC H10D64/257 (20250101); **H10D30/475** (20250101); **H10D64/01** (20250101); **H10D64/111** (20250101); **H10D64/519** (20250101);

Background/Summary

REFERENCE TO RELATED APPLICATIONS [0001] This Application is a Continuation of U.S. application Ser. No. 18/302,174, filed on Apr. 18, 2023, which is a Continuation of U.S. application Ser. No. 17/144,671, filed on Jan. 8, 2021 (now U.S. Pat. No. 11,664,431, issued on May 30, 2023). The contents of the above-referenced Patent Applications are hereby incorporated by reference in their entirety.

BACKGROUND

[0002] Modern-day integrated chips comprise millions or billions of transistor devices formed on a semiconductor substrate (e.g., silicon). Integrated chips (ICs) may use many different types of transistor devices, depending on an application of an IC. In recent years, the increasing market for cellular and RF (radio frequency) devices has resulted in a significant increase in the use of high voltage transistor devices. For example, high voltage transistor devices are often used in power amplifiers for RF transmission/receiving chains due to their ability to handle high breakdown voltages (e.g., greater than about 50V) and high frequencies. High voltage devices are also used in power management integrated circuits, automotive electronics, sensor interfaces, flat panel display driver applications, etc.

Description

BRIEF DESCRIPTION OF THE DRAWINGS

[0003] Aspects of the present disclosure are best understood from the following detailed description when read with the accompanying figures. It is noted that, in accordance with the standard practice in the industry, various features are not drawn to scale. In fact, the dimensions of the various features may be arbitrarily increased or reduced for clarity of discussion.

[0004] FIGS. 1A-1B illustrate some embodiments of an integrated chip having a transistor device comprising a gate structure that is wrapped around a first source/drain contact to provide isolation between the first source/drain contact and a second source/drain contact.

[0005] FIGS. 2A-2B illustrate some additional embodiments of an integrated chip having a transistor device comprising gate structures wrapped around first source/drain contacts.

[0006] FIG. 3A illustrates a top-view of some embodiments of an integrated chip having a transistor device comprising gate structures wrapped around source contacts.

[0007] FIG. 3B illustrates a top-view of some embodiments of an integrated chip having a transistor device comprising gate structures wrapped around drain contacts.

[0008] FIG. 4 illustrates a graph showing some embodiments of a drain current as a function of gate voltage for a disclosed transistor device.

[0009] FIG. 5 illustrates a top-view of some embodiments of an integrated chip having a transistor device comprising gate structures wrapped around first source/drain contacts arranged in a two-dimensional array.

[0010] FIG. 6 illustrates a cross-sectional view of some embodiments of a HEMT (high electron

mobility transistor) device comprising gate structures wrapped around first source/drain contacts. [0011] FIG. 7 illustrates a cross-sectional view of some embodiments of a MISFET (metal-insulator-semiconductor field-effect-transistor) device comprising gate structures wrapped around first source/drain contacts.

[0012] FIGS. 8A-8B illustrate some embodiments of an integrated chip having a transistor device comprising gate structures wrapped around first source/drain contacts and surrounded by an isolation region.

[0013] FIG. 9 illustrates some additional embodiments of an integrated chip having a transistor device comprising gate structures wrapped around first source/drain contacts and surrounded by an isolation region.

[0014] FIGS. 10A-10C illustrate top-views of some alternative embodiments of integrated chips having transistor devices comprising gate structures and/or a second source/drain contact with different shapes.

[0015] FIGS. 11A-11B illustrate some embodiments of an integrated chip having a transistor device comprising field plates wrapped around first source/drain contacts.

[0016] FIGS. 12A-21 illustrate some embodiments of a method of forming an integrated chip having a HEMT device comprising gate structures wrapped around first source/drain contacts.

[0017] FIG. 22 illustrates a flow diagram of some embodiments of a method of forming an integrated chip having a HEMT device comprising gate structures wrapped around first source/drain contacts.

[0018] FIGS. 23A-29 illustrate some embodiments of a method of forming an integrated chip having a MISFET device comprising gate structures wrapped around first source/drain contacts.

[0019] FIG. 30 illustrates a flow diagram of some embodiments of a method of forming an integrated chip having a MISFET device comprising gate structures wrapped around first source/drain contacts.

DETAILED DESCRIPTION

[0020] The following disclosure provides many different embodiments, or examples, for implementing different features of the provided subject matter. Specific examples of components and arrangements are described below to simplify the present disclosure. These are, of course, merely examples and are not intended to be limiting. For example, the formation of a first feature over or on a second feature in the description that follows may include embodiments in which the first and second features are formed in direct contact, and may also include embodiments in which additional features may be formed between the first and second features, such that the first and second features may not be in direct contact. In addition, the present disclosure may repeat reference numerals and/or letters in the various examples. This repetition is for the purpose of simplicity and clarity and does not in itself dictate a relationship between the various embodiments and/or configurations discussed.

[0021] Further, spatially relative terms, such as “beneath,” “below,” “lower,” “above,” “upper” and the like, may be used herein for ease of description to describe one element or feature's relationship to another element(s) or feature(s) as illustrated in the figures. The spatially relative terms are intended to encompass different orientations of the device in use or operation in addition to the orientation depicted in the figures. The apparatus may be otherwise oriented (rotated 90 degrees or at other orientations) and the spatially relative descriptors used herein may likewise be interpreted accordingly.

[0022] High-voltage transistor devices are used in many modern-day electronic devices. As the size of semiconductor devices continues to shrink, there has been an increased interest in high voltage devices that utilize two-dimensional electron gases (2 DEGs). Such high voltage devices are typically formed on stacked substrates comprising a plurality of semiconductor layers. The plurality of semiconductor layers include an active layer and a barrier layer that contacts an upper surface of the active layer to form a heterojunction at their interface. A 2 DEG is inherently present

at the heterojunction between the active layer and the barrier layer. Because a 2 DEG is inherently present between the active layer and the barrier layer, electrons are able to move freely along the interface.

[0023] 2 DEG based transistor devices may comprise an active area surrounded by an isolation region. The isolation region has a damaged crystalline lattice that confines a 2 DEG within the active area by disrupting the 2 DEG and mitigating movement of electrons. A source contact and a drain contact are disposed over the active area. To prevent unwanted currents from flowing between the source contact and the drain contact (i.e., to form a device in a “normally off” mode), a gate structure comprising a doped semiconductor material (e.g., p-doped gallium nitride (GaN)) may be disposed within the active area between the source contact and the drain contact. The gate structure is able to interrupt the underlying 2 DEG so as to prevent electrons from moving freely under the gate structure.

[0024] The gate structure may extend over an entire width of the active area as an elongated or rectangular shaped ‘gate finger.’ By having the gate structure extending over an entire width of the active area, the movement of electrons between the source contact and the drain contact can be blocked within the active area. However, it has been appreciated that the isolation region does not provide complete isolation, and that there may be unwanted leakage currents that flow around ends of a gate finger and through the isolation region. The unwanted leakage currents can result in a sub-threshold hump in a drain current vs. gate voltage relation of a transistor device. The sub-threshold hump has a number of negative consequences, such as higher power consumption and being difficult to model (e.g., in SPICE curve fitting and/or parameter extraction).

[0025] The present disclosure, in some embodiments, relates to an integrated chip that has a transistor device comprising a gate structure that is configured to provide improved isolation between source/drain contacts. The gate structure wraps around a first source/drain contact and a second source/drain contact that wraps around the gate structure. Because the gate structure is able to disrupt an underlying two-dimensional electron gas (2 DEG) within the substrate, having the gate structure wrap around the first source/drain contact disrupts the 2 DEG along a closed and unbroken path surrounding the first source/drain contact. Disrupting the 2 DEG along a closed and unbroken path that surrounds the first source/drain contact improves performance of the transistor device (e.g., reduces a sub-threshold hump in the drain current vs. gate voltage relation of the transistor device) by mitigating leakage between the first source/drain contact and the second source/drain contact.

[0026] FIGS. **1A-1B** illustrate some embodiments of an integrated chip having a transistor device comprising a gate structure that is wrapped around a source/drain contact. FIG. **1A** illustrates a top-view **100** of the integrated chip taken along line A-A’ of FIG. **1B**. FIG. **1B** illustrates a cross-sectional view **114** of the integrated chip taken along line B-B’ of FIG. **1A**.

[0027] As shown in top-view **100** of FIG. **1A**, the integrated chip comprises a transistor device having a first source/drain contact **104**, a gate structure **106**, and a second source/drain contact **108** disposed over a stacked substrate **102**. The first source/drain contact **104** and the second source/drain contact **108** are separated by the gate structure **106** along a first direction **110** and along a second direction **112** that is perpendicular to the first direction **110**. In some embodiments, the first source/drain contact **104** may comprise a source contact and the second source/drain contact **108** may comprise a drain contact. In such embodiments, a source contact is surrounded by the gate structure **106** and the gate structure **106** is surrounded by a drain contact. In other embodiments, the first source/drain contact **104** may comprise a drain contact and the second source/drain contact **108** may comprise a source contact, so that a drain contact is surrounded by the gate structure **106** and the gate structure **106** is surrounded by a source contact.

[0028] As shown in cross-sectional view **114** of FIG. **1B**, the stacked substrate **102** comprises a plurality of different layers stacked onto one another. In some embodiments, the stacked substrate **102** comprises an active layer **120** (e.g., a channel layer) disposed over a base substrate **116** and a

barrier layer **122** disposed over the active layer **120**. In some embodiments, a buffer layer **118** may be disposed between the active layer **120** and the base substrate **116** to improve lattice matching between the base substrate **116** and the active layer **120**. The active layer **120** and the barrier layer **122** meet at an interface that defines a heterojunction in which a two-dimensional electron gas (2 DEG) **121** is present. An inter-level dielectric (ILD) layer **124** is disposed over the stacked substrate **102**. A plurality of conductive contacts **126** extend through the ILD layer **124** to contact the first source/drain contact **104**, the gate structure **106**, and the second source/drain contact **108**. [0029] As shown in top-view **100** of FIG. **1A**, the gate structure **106** wraps around the first source/drain contact **104** along a first closed loop or a first closed path (e.g., a continuous and unbroken path). The second source/drain contact **108** wraps around the gate structure **106**. In some embodiments, the second source/drain contact **108** wraps around the gate structure **106** along a second closed loop or second closed path (e.g., a continuous and unbroken path).

[0030] The gate structure **106** is configured to disrupt the 2 DEG **121** within the stacked substrate **102**. Because the gate structure **106** wraps around the first source/drain contact **104** along the first closed loop, the gate structure **106** is able to disrupt the 2 DEG **121** along a continuous path that separates the first source/drain contact **104** and the second source/drain contact **108**. By disrupting the 2 DEG **121** along a continuous path that separates the first source/drain contact **104** and the second source/drain contact **108**, currents are not able to leak around ends of the gate structure **106**. Therefore, the gate structure **106** is able to provide for good isolation between the first source/drain contact **104** and the second source/drain contact **108**. The isolation provided by the gate structure **106** may mitigate a sub-threshold hump in a drain current vs. gate voltage relation of the transistor device even without an isolation region.

[0031] FIGS. **2A-2B** illustrate some embodiments of an integrated chip having a transistor device comprising gate structures wrapped around first source/drain contacts. FIG. **2A** illustrates a top-view **200** of the integrated chip taken along line A-A' of FIG. **2B**. FIG. **2B** illustrates a cross-sectional view **206** of the integrated chip taken along line B-B' of FIG. **2A**.

[0032] As shown in top-view **200** of FIG. **2A**, the integrated chip comprises a transistor device having a plurality of first source/drain contacts **104a-104c** that are separated from one another along a first direction **110**. A plurality of gate structures **106a-106c** are disposed over the stacked substrate **102** and are interleaved between the plurality of first source/drain contacts **104a-104c** along the first direction **110**. The plurality of gate structures **106a-106c** are separated from one another along the first direction **110** and are separated from the plurality of first source/drain contacts **104a-104c** along the first direction **110** and along a second direction **112** that is perpendicular to the first direction **110**. The plurality of gate structures **106a-106c** wrap around respective ones of the plurality of first source/drain contacts **104a-104c**. For example, a first gate structure **106a** wraps around first source/drain contact **104a** and a second gate structure **106b** wraps around first source/drain contact **104b**. Although top-view **200** is illustrated as having three gate structures and three first source/drain contacts it will be appreciated that in various embodiments, a disclosed transistor device may comprise tens, hundreds, or thousands of gate structures and first source/drain contacts.

[0033] A second source/drain contact **108** is also disposed over the stacked substrate **102**. The second source/drain contact **108** continuously extends in the first direction **110** past outermost ones of the plurality of first source/drain contacts **104a-104c**. In some embodiments, the second source/drain contact **108** continuously wraps around the plurality of gate structures **106a-106c** and the plurality of first source/drain contacts **104a-104c**. The second source/drain contact **108** comprises a plurality of loops **202a-202c** that are coupled together. For example, the second source/drain contact **108** may comprise a first loop **202a**, a second loop **202b**, and a third loop **202c**. In some embodiments, the plurality of loops **202a-202c** are respectively defined by one or more curved sidewalls of the second source/drain contact **108**.

[0034] The plurality of loops **202a-202c** comprise a plurality of interior sidewalls **108i** that define a

plurality of openings **204a-204c** extending through the second source/drain contact **108**. In some embodiments, the plurality of openings **204a-204c** are separated from one another along the first direction **110**. Respective ones of the plurality of gate structures **106a-106c** and the plurality of first source/drain contacts **104a-104c** are disposed within respective ones of the plurality of openings **204a-204c**. For example, first source/drain contact **104a** and first gate structure **106a** are disposed within a first opening **204a**, first source/drain contact **104b** and second gate structure **106b** are disposed within a second opening **204b**, etc.

[0035] In various embodiments, the plurality of first source/drain contacts **104a-104c** respectively comprise a rectangular shape, a rounded rectangular shape, a square shape, a rounded square shape, or the like. In various embodiments, the plurality of gate structures **106a-106c** and the second source/drain contact **108** may respectively comprise a circular shape, an oval shape, a rounded rectangular shape, a hexagonal shape, a racetrack shape, or the like. In some embodiments, the plurality of gate structures **106a-106c** comprise line segments **107L** and end segments **107e**. The line segments **107L** extend in the second direction **112** along opposing sides of the plurality of first source/drain contacts **104a-104c**. In some embodiments, the line segments **107L** may extend past opposing ends of the plurality of first source/drain contacts **104a-104c**. The end segments **107e** wrap around ends of the plurality of first source/drain contacts **104a-104c** to couple together adjacent ones of the line segments **107L**. In various embodiments, the end segments **107e** may have a curved sidewall that define a semi-circular shape, a semi-oval shape, a semi-hexagonal shape with rounded corners, or the like. In some embodiments, a rounded shape of the end segments **107e** may reduce crowding of electric field lines generated by the plurality of gate structures **106a-106c**. In some embodiments, the line segments **107L** may define a central region of the plurality of openings **204a-204c** having a substantially constant width, while the end segments **107e** may define end regions of the openings **204a-204c** that have widths that decrease as a distance from the central region increases. In some embodiments, the second source/drain contact **108** may also comprise line segments **109L** and end segments **109e**.

[0036] As shown in cross-sectional view **206** of FIG. 2B, the stacked substrate **102** comprises an active layer **120** disposed over a base substrate **116** and a barrier layer **122** disposed over the active layer **120**. In some embodiments, a buffer layer **118** may be disposed between the active layer **120** and the base substrate **116**. The active layer **120** and the barrier layer **122** meet at an interface that defines a heterojunction at which a two-dimensional electron gas (2 DEG) **121** is present. In various embodiments, the base substrate **116** may comprise silicon, silicon carbide, sapphire, or the like. In some embodiments, the active layer **120** may comprise gallium nitride (GaN), gallium arsenide (GaAs), or the like. In some embodiments, the barrier layer **122** may comprise aluminum gallium nitride (AlGaN), aluminum gallium arsenide (AlGaAs), or the like. In some embodiments, the buffer layer **118** may comprise GaN (having different concentrations of Ga and N than the active layer **120**), GaAs (having a different concentration of Ga and As than the active layer **120**), or the like.

[0037] In some embodiments, the plurality of gate structures **106a-106c** respectively comprise a lower gate layer **208** and a gate contact **210** over the lower gate layer **208**. Both the lower gate layer **208** and the gate contact **210** of the plurality of gate structures **106a-106c** wrap around the plurality of first source/drain contacts **104a-104c** in closed loops. In various embodiments, the gate contact **210** may comprise a metal, such as aluminum, cobalt, titanium, tungsten, or the like. In some embodiments, the transistor device is a high electron mobility transistor (HEMT) device and the lower gate layer **208** is a doped semiconductor material, such as p-doped gallium nitride, for example. The doped semiconductor material allows the plurality of gate structures **106a-106c** to interrupt the underlying 2 DEG **121** so as to form a “normally-off” device. In other embodiments, the transistor device is a metal-insulator-semiconductor field-effect-transistor (MISFET) device and the lower gate layer **208** is an insulating material, such as silicon dioxide, silicon nitride, or the like.

[0038] An ILD layer **124** is disposed over the stacked substrate **102**. Conductive contacts **126**

extend through the ILD layer **124** to contact the plurality of first source/drain contacts **104a-104c**, the plurality of gate structures **106a-106c**, and the second source/drain contact **108**. In some embodiments (not shown), additional interconnect layers (e.g., interconnect wires and/or interconnect vias) may be disposed within additional ILD layers over the ILD layer **124**. The additional interconnect layers may comprise a plurality of conductive interconnects that are configured to electrically couple the plurality of first source/drain contacts **104a-104c** and to electrically couple the plurality of gate structures **106a-106c**. Because the plurality of first source/drain contacts **104a-104c** and the plurality of gate structures **106a-106c** are respectively electrically coupled together, the plurality of first source/drain contacts **104a-104c** and the plurality of gate structures **106a-106c** operate as a single transistor device.

[0039] In various embodiments, the conductive contacts **126** may be disposed at different locations on the second source/drain contact **108**. For example, in some embodiments the conductive contacts **126** may be disposed on one of the line segments **109L** of the second source/drain contact **108**, while in other embodiments the conductive contacts **126** may be disposed on one of the end segments **109e** of the second source/drain contact **108**. In some embodiments, multiple conductive contacts may be disposed on the second source/drain contact **108**. In other embodiments, a single conductive contact may be disposed on the second source/drain contact **108**.

[0040] FIG. 3A illustrates a top-view of some embodiments of an integrated chip having a transistor device comprising gate structures wrapped around source contacts.

[0041] The integrated chip **300** comprises a transistor device having a plurality of source contacts **302a-302b** separated along a first direction **110**. A plurality of gate structures **106a-106b** wrap around the plurality of source contacts **302a-302b** and a drain contact **304** wraps around the plurality of gate structures **106a-106b**. Having the drain contact **304** wrap around the gate structures **106a-106b** may improve device performance by allowing a high voltage that is applied to the drain contact **304** to be spread out over a relatively large area.

[0042] In some embodiments, the plurality of source contacts **302a-302b** have a first width **306** and the drain contact **304** has a second width **308**. In some embodiments, the first width **306** and the second width **308** may be larger than a third width **310** of the plurality of gate structures **106a-106b**. In some embodiments, the first width **306** and/or the second width **308** may be between approximately 100% and approximately 200% larger than the third width **310**, between approximately 50% and approximately 250% larger than the third width **310**, or other suitable values. The greater widths of the plurality of source contacts **302a-302b** and the drain contact **304** allows for overlying interconnects (e.g., conductive contacts) to form good electrical connections with the plurality of source contacts **302a-302b** and the drain contact **304** at large voltages (e.g., greater than approximately 100V, greater than approximately 200V, or the like).

[0043] In some embodiments, the plurality of gate structures **106a-106b** are separated from the plurality of source contacts **302a-302b** by a first distance **312** and from the drain contact **304** by a second distance **314** that is larger than the first distance **312**. In some embodiments, the first distance **312** may be in a range of between approximately 1 μm and approximately 15 μm , between approximately 2 μm and approximately 10 μm , or other suitable values. In some embodiments, the second distance **314** may be in a range of between approximately 5 μm and approximately 150 μm , between approximately 10 μm and approximately 100 μm , or other suitable values. By having the second distance **314** larger than the first distance **312**, a breakdown voltage of a device can be increased.

[0044] Although the integrated chip **300** of FIG. 3A illustrates a transistor device having a plurality of source contacts **302a-302b** surrounded by a drain contact **304**, it will be appreciated that the isolation provided by the plurality of gate structures **106a-106b** allows for positions of the plurality of source contacts **302a-302b** and the drain contact **304** to be switched. For example, FIG. 3B illustrates a top-view of some embodiments of an integrated chip **316** having a transistor device comprising a plurality of gate structures **106a-106b** wrapped around a plurality of drain contacts

304a-304b and a second source contact **302** wrapped around the plurality of gate structures **106a-106b**.

[0045] FIG. **4** illustrates a graph **400** showing some embodiments of a drain current as a function of a gate voltage for a disclosed transistor device.

[0046] Graph **400** illustrates a gate voltage $V_{\text{sub.g}}$ along an x-axis and a drain current ($I_{\text{sub.d}}$) along a y-axis. The drain current of a transistor device having rectangular shaped gate fingers is shown by line **402**. The drain current of a transistor device having the disclosed gate structure (e.g., a gate structure that wraps around a first source/drain contact as illustrated, for example, in FIG. **1**) is shown by line **404**. As shown in graph **400**, the drain current shown by line **402** has a larger sub-threshold hump **406** than that of the drain current shown by line **404**.

[0047] FIG. **5** illustrates a top-view of some embodiments of an integrated chip **500** having a transistor device comprising gate structures wrapped around first source/drain contacts arranged in a two-dimensional array.

[0048] The integrated chip **500** comprises a transistor device having a plurality of first source/drain contacts **104x**, a plurality of gate structures **106x**, and a second source/drain contact **108** disposed over a stacked substrate **102**. The plurality of first source/drain contacts **104x** and the plurality of gate structures **106x** are separated along a first direction **110** and along a second direction **112** that is perpendicular to the first direction **110**.

[0049] The second source/drain contact **108** comprises a plurality of loops **202a-202g** that are coupled together as a continuous structure that wraps around the plurality of first source/drain contacts **104x** and the plurality of gate structures **106x**. In some embodiments, the plurality of loops **202a-202g** are arranged in a two-dimensional array extending along the first direction **110** and the second direction **112**. For example, the plurality of loops **202a-202g** may comprise a first plurality of loops **202a-202d** arranged along a first row **502a** and a second plurality of loops **202e-202g** arranged along a second row **502b** that is laterally offset from the first row **502a**. In some embodiments, one or more openings **504** may be present between the first plurality of loops **202a-202d** and the second plurality of loops **202e-202g**. By arranging the plurality of loops **202a-202g** in a two dimensional array, a design flexibility of the device can be increased.

[0050] It will be appreciated that in various embodiments, the disclosed transistor device may be any transistor device that utilizes a 2 DEG. FIGS. **5-6** illustrates some embodiments of integrated chips having different types of transistor devices. FIGS. **5-6** are non-limiting examples of transistor devices that may utilize the disclosed gate structures and one of ordinary skill in the art will appreciate that other types of transistor devices may also be used.

[0051] FIG. **6** illustrates some embodiments of an integrated chip **600** having a high electron mobility transistor (HEMT) device comprising gate structures wrapped around first source/drain contacts.

[0052] The integrated chip **600** comprises a HEMT device having a plurality of first source/drain contacts **104a-104b**, a plurality of gate structures **106a-106b**, and a second source/drain contact **108** disposed over a stacked substrate **102**. The plurality of gate structures **106a-106b** respectively comprise a doped semiconductor material **602** and a gate contact **210** over the doped semiconductor material **602**. In some embodiments, the doped semiconductor material **602** may comprise p-doped gallium nitride. In some embodiments, one or more sidewalls of the doped semiconductor material **602** may be laterally offset from one or more sidewalls of the gate contact **210**.

[0053] A passivation layer **604** extends over the plurality of first source/drain contacts **104a-104b** and the second source/drain contact **108**. The passivation layer **604** also extends over the doped semiconductor material **602** of the plurality of gate structures **106a-106b**. The gate contact **210** extends through the passivation layer **604** to contact the doped semiconductor material **602**. In various embodiments, the passivation layer **604** may comprise an oxide (e.g., silicon oxide), a nitride (e.g., silicon nitride), or the like.

[0054] FIG. **7** illustrates some additional embodiments of an integrated chip **700** having a MISFET

(metal-insulator-semiconductor field effect transistor) device comprising gate structures wrapped around first source/drain contacts.

[0055] The integrated chip **700** comprises a MISFET device having a plurality of first source/drain contacts **104a-104c**, a plurality of gate structures **106a-106c**, and a second source/drain contact **108** disposed over a stacked substrate **102**. The plurality of gate structures **106a-106c** respectively comprise an insulating material **702** and a gate contact **210** over the insulating material **702**. In some embodiments, the insulating material **702** may comprise an oxide (e.g., silicon oxide), a nitride (e.g., silicon nitride), or the like. In some embodiments, sidewalls of the insulating material **702** may be substantially aligned with sidewalls of the gate contact **210**.

[0056] FIGS. **8A-8B** illustrate some embodiments of an integrated chip having a transistor device comprising gate structures wrapped around first source/drain contacts and surrounded by an isolation region.

[0057] As shown in cross-sectional view **800** of FIG. **8A**, the integrated chip comprises an active area **802** disposed within a stacked substrate **102**. The stacked substrate **102** comprises an active layer **120** disposed over a base substrate **116** and a barrier layer **122** disposed over the active layer **120**. In some embodiments, a buffer layer **118** may be disposed between the active layer **120** and the base substrate **116**. A 2 DEG **121** is present at an interface of the active layer **120** and the barrier layer **122**.

[0058] The active area **802** is surrounded by an isolation region **804**. In some embodiments, the isolation region **804** may comprise a region of the stacked substrate **102** in which crystalline structures of one or more layers of the stacked substrate **102** are damaged (e.g., by way of an ion implantation process). The crystalline damage within the one or more layers disrupts the 2 DEG **121**, so as to prevent the 2 DEG **121** from extending into the isolation region **804**.

[0059] As shown in top-view **806** of FIG. **8B**, the active area **802** is surrounded by the isolation region **804** along a first direction **110** and along a second direction **112** that is perpendicular to the first direction **110**. The active area **802** has a length **808** extending along the first direction **110** and a width **810** extending along the second direction **112**. In some embodiments, the length **808** is larger than the width **810**.

[0060] A plurality of first source/drain contacts **104a-104c**, a plurality of gate structures **106a-106c**, and a second source/drain contact **108** are disposed over the active area **802**. The second source/drain contact **108** continuously wraps around the plurality of gate structures **106a-106c** and the plurality of first source/drain contacts **104a-104c**. In some embodiments, the active area **802** extends past outermost sidewalls of the second source/drain contact **108** along the first direction **110** and/or along the second direction **112**. In other embodiments (not shown), a part of the plurality of first source/drain contacts **104a-104c** may extend to over the isolation region **804**. For example, the plurality of first source/drain contacts **104a-104c** may extend along the second direction **112** over the isolation region **804**.

[0061] FIG. **9** illustrates a top-view of an integrated chip **900** having a transistor device comprising gate structures wrapped around first source/drain contacts and surrounded by an isolation region.

[0062] The integrated chip **900** comprises an active area **902** surrounded by an isolation region **804** along a first direction **110** and along a second direction **112**. A plurality of gate structures **106x** are disposed over the active area **902** around a plurality of first source/drain contacts **104x**. The active area **902** has a first width **904** and a second width **906** that is larger than the first width **904**. In some embodiments, the active area **902** comprises a plurality of curved edges **908** that extend between the first width **904** and the second width **906**. In some embodiments, the plurality of curved edges **908** are substantially conformal to curved outer sidewalls of the second source/drain contact **108**. The curved edges **908** allow the isolation region **804** to provide for greater isolation over a smaller area.

[0063] FIG. **10A** illustrates a top-view of some alternative embodiments of an integrated chip **1000** having a transistor device comprising gate structures and/or a second source/drain contact with

different shapes.

[0064] The integrated chip **1000** comprises a transistor device having a plurality of gate structures **106a-106d** disposed within an active area **802** of a substrate **102** and separated along a first direction **110**. The plurality of gate structures **106a-106d** respectively surround one of a plurality of first source/drain contacts **104a-104d** and are separated from one another by a second source/drain contact **108**.

[0065] The plurality of gate structures **106a-106d** comprise a first gate structure **106a** disposed along a first end of the active area **802** and a last gate structure **106d** disposed along a second end of the active area **802** opposing the first end. The first gate structure **106a** and the last gate structure **106d** are outermost gate structures (i.e., are at opposing ends of a series of gate structures over the active area **802**). The first gate structure **106a** is separated from the last gate structure **106d** by way of a plurality of central gate structures **106b-106c**. In some embodiments, the first gate structure **106a** and the last gate structure **106d** may have different shapes than the plurality of central gate structures **106b-106c**.

[0066] For example, in some embodiments the first gate structure **106a** may wrap around first source/drain contact **104a** along a continuous path that extends between a first end **1001a** disposed along a first side of first source/drain contact **104a** and a second end **1001b** disposed along the first side of first source/drain contact **104a**. The first end **1001a** is separated from the second end **1001b** by a non-zero distance **1003** (e.g., so that the first gate structure **106a** is in the shape of a “C”). In some embodiments, the first gate structure **106a** and/or the last gate structure **106d** may have ends comprising sidewalls that define a first opening **1002** along an outer edge of the first gate structure **106a** and/or the last gate structure **106d**, which faces away from the active area **802**. Because there is a first opening **1002** along an outer edge of the first gate structure **106a** and/or the last gate structure **106d**, the first gate structure **106a** and/or the last gate structure **106d** extend part way, but not completely, around a first source/drain contact **104a** and/or a last source/drain contact **104d**, respectively. In contrast, the central gate structures **106b-106c** extend completely around first source/drain contacts, **104b** and **104c**, in closed and continuous loops.

[0067] In some embodiments, the second source/drain contact **108** may also have sidewalls that define a second opening **1004** along an outer edge of the second source/drain contact **108**, which faces away from the active area **802**. Because there is a second opening **1004** along an outer edge of the second source/drain contact **108**, the second source/drain contact **108** extends part way, but not completely, around the first source/drain contact **104a** and/or the last source/drain contact **104d**. In contrast, the second source/drain contact **108** extends completely around first source/drain contacts, **104b** and **104c**, in closed and continuous loops.

[0068] In some embodiments, the first opening **1002** and the second opening **1004** may have substantially equal sizes. In other embodiments, the plurality of gate structures **106a-106d** and the second source/drain contact **108** may define openings that have different sizes. By having openings with different sizes, a size of the transistor device can be changed and a leakage of the transistor device can be varied. For example, as shown in top-view **1006** of FIG. **10B**, the first gate structure **106a** and the last gate structure **106d** may have a first opening **1002** that is smaller than a second opening **1008** within the second source/drain contact **108**. By having the second opening **1008** larger than the first opening **1002**, leakage between the plurality of first source/drain contacts **104a-104d** and the second source/drain contact **108** can be further reduced. In yet other embodiments, shown in top-view **1010** of FIG. **10C**, the second source/drain contact **108** may have an opening **1012** along outer edges, while the first gate structure **106a** and the last gate structure **106d** extend in closed loops (i.e., so that the first gate structure and the last gate structure do not have an opening).

[0069] FIGS. **11A-11B** illustrate some embodiments of integrated chips having a transistor device comprising field plates wrapped around source/drain contacts. FIG. **11A** illustrates a cross-sectional view **1100** of the integrated chip taken along line A-A' of FIG. **11B**. FIG. **11B** illustrates a top-view

1104 of the integrated chip taken along line B-B' of FIG. **11A**. For ease of illustration, the passivation layer **604** has been omitted from top-view **1104**.

[0070] As shown in cross-sectional view **1100** of FIG. **11A**, the integrated chip comprises a transistor device having a plurality of first source/drain contacts **104a-104c** and a plurality of gate structures **106a-106c** disposed over a stacked substrate **102**. The plurality of gate structures **106a-106c** are interleaved between the plurality of first source/drain contacts **104a-104c** along the first direction **110**. A second source/drain contact **108** is disposed over the stacked substrate **102** and continuously wraps around the plurality of gate structures **106a-106c** and the plurality of first source/drain contacts **104a-104c**.

[0071] A plurality of field plates **1102a-1102c** are disposed over the stacked substrate **102** between the plurality of first source/drain contacts **104a-104c** and the second source/drain contact **108**. In some embodiments, the plurality of field plates **1102a-1102c** may be located between the plurality of first source/drain contacts **104a-104c** and the plurality of gate structures **106a-106c**. In some such embodiments, the plurality of first source/drain contacts **104a-104c** may comprise a plurality of drain contacts and the second source/drain contact **108** may comprise a source contact, so that the plurality of field plates **1102a-1102c** are between the plurality of gate structures **106a-106c** and the plurality of drain contacts. In other embodiments, the plurality of field plates **1102a-1102c** may be located between the plurality of gate structures **106a-106c** and the second source/drain contact **108**. In some such embodiments, the plurality of first source/drain contacts **104a-104c** may comprise a plurality of source contacts and the second source/drain contact **108** may comprise a drain contact, so that the plurality of field plates **1102a-1102c** are between the plurality of gate structures **106a-106c** and the drain contact.

[0072] In some embodiments, the plurality of field plates **1102a-1102c** may be electrically coupled to the plurality of gate structures **106a-106c**. In other embodiments (not shown), the plurality of field plates **1102a-1102c** may be electrically coupled to the plurality of first source/drain contacts **104a-104c** or the second source/drain contact **108**. In some embodiments, the plurality of field plates **1102a-1102c** may be disposed laterally adjacent to the plurality of gate structures **106a-106c** and/or the plurality of first source/drain contacts **104a-104c**. In other embodiments, the plurality of field plates **1102a-1102c** may be located higher in a back-end of the line (BEOL) stack. For example, the plurality of field plates **1102a-1102c** may be located on an interconnect layer that is over ILD layer **124**.

[0073] As shown in top-view **1104** of FIG. **11B**, the plurality of field plates **1102a-1102c** wrap around the plurality of first source/drain contacts **104a-104c** so as to extend past opposing sides of the first source/drain contacts **104a-104c** along the first direction **110** and along the second direction **112**. In some embodiments, the plurality of field plates **1102a-1102c** wrap around the plurality of first source/drain contacts **104a-104c** in closed loops.

[0074] FIGS. **12A-21** illustrate some embodiments of a method of forming an integrated chip having a high electron mobility (HEMT) device comprising gate structures wrapped around first source/drain contacts. Although FIGS. **12A-21** are described in relation to a method, it will be appreciated that the structures disclosed in FIGS. **12A-21** are not limited to such a method, but instead may stand alone as structures independent of the method.

[0075] As shown in cross-sectional view **1200** of FIG. **12A** and top-view **1206** of FIG. **12B**, an epitaxial stack **1202** is formed over a base substrate **116** to define a stacked substrate **102**. In some embodiments, the epitaxial stack **1202** may comprise an active layer **120** formed over the base substrate **116**, a barrier layer **122** formed on the active layer **120**, and a doped semiconductor layer **1204** formed on the barrier layer **122**. In some embodiments, the epitaxial stack **1202** may further comprise a buffer layer **118** formed onto the base substrate **116** prior to the formation of the active layer **120**.

[0076] In various embodiments, the base substrate **116** may comprise silicon, silicon carbide, sapphire, or the like. In some embodiments, the active layer **120** may comprise gallium nitride

(GaN), gallium arsenide (GaAs), or the like. In some embodiments, the barrier layer **122** may comprise aluminum gallium nitride (AlGaN), aluminum gallium arsenide (AlGaAs), or the like. In some embodiments, the buffer layer **118** may comprise GaN (having different concentrations of Ga and N than the active layer **120**), GaAs (having different concentrations of Ga and As than the active layer **120**), or the like. In some embodiments, the buffer layer **118**, the active layer **120**, the barrier layer **122**, and the doped semiconductor layer **1204** may be epitaxially grown onto the base substrate **116** by way of chemical vapor deposition processes, physical vapor deposition processes, and/or the like.

[0077] As shown in cross-sectional view **1300** of FIG. **13A** and top-view **1306** of FIG. **13B**, the doped semiconductor layer (**1204** of FIGS. **12A-12B**) may be selectively patterned according to a first masking layer **1302**. Patterning the doped semiconductor layer results in a doped semiconductor material **602** having a plurality of interior sidewalls that define a plurality of cavities **1308** that extends through the doped semiconductor material **602**. In some embodiments, the plurality of interior sidewalls extend along closed and unbroken paths that surrounds the plurality of cavities **1308**. In some embodiments, the doped semiconductor layer may be selectively patterned by exposing the doped semiconductor layer to a first etchant **1304** according to the first masking layer **1302**. In some embodiments, the first masking layer **1302** may comprise a photosensitive material (e.g., photoresist). In various embodiments, the first etchant **1304** may comprise a wet etchant or a dry etchant.

[0078] As shown in cross-sectional view **1400** of FIG. **14A** and top-view **1410** of FIG. **14B**, the epitaxial stack **1202** may be selectively patterned according to a second masking layer **1402** to form a plurality of first source/drain recesses **1404** and a second source/drain recess **1406**. In some embodiments, the plurality of first source/drain recesses **1404** and the second source/drain recess **1406** may extend through the barrier layer **122** and into the active layer **120**. In some embodiments, the epitaxial stack **1202** may be selectively patterned by exposing the epitaxial stack **1202** to a second etchant **1408** according to the second masking layer **1402**. In some embodiments, the second masking layer **1402** may comprise a photosensitive material (e.g., photoresist). In various embodiments, the second etchant **1408** may comprise a wet etchant or a dry etchant.

[0079] As shown in cross-sectional view **1500** of FIG. **15A** and top-view **1502** of FIG. **15B**, a conductive material is formed within the plurality of first source/drain recesses **1404** to define a plurality of first source/drain contacts **104x** over the stacked substrate **102**. The conductive material is also formed within the second source/drain recess **1406** to define a second source/drain contact **108** over the stacked substrate **102**. The second source/drain contact **108** wraps around the plurality of first source/drain contacts **104x** as a continuous structure. In various embodiments, the conductive material may comprise a metal, such as aluminum, tungsten, titanium, cobalt, or the like. In some embodiments, the conductive material may be formed by a deposition process (e.g., CVD, PVD, sputtering, PE-CVD, or the like) and/or a plating process (e.g., an electroplating process, an electro-less plating process, or the like). In some embodiments, a planarization process (e.g., a chemical mechanical planarization process) may be performed after forming the conductive material.

[0080] In some alternative embodiments (not shown), the plurality of first source/drain contacts **104x** and the second source/drain contact **108** may be formed over a topmost surface of the barrier layer **122** without forming the plurality of first source/drain recesses and the second source/drain recess. In such embodiments, the plurality of first source/drain contacts **104x** and the second source/drain contact **108** have bottommost surfaces that are over the barrier layer **122**.

[0081] As shown in cross-sectional view **1600** of FIG. **16A** and top-view **1602** of FIG. **16B**, a passivation layer **604** is formed over the plurality of first source/drain contacts **104x**, the second source/drain contact **108**, and the stacked substrate **102**. In various embodiments, the passivation layer **604** may comprise an oxide (e.g., silicon dioxide), a nitride (e.g., silicon nitride), a carbide (e.g., silicon carbide), or the like. In some embodiments, the passivation layer **604** may be formed

by a deposition process (e.g., CVD, PVD, sputtering, PE-CVD, or the like).

[0082] As shown in cross-sectional view **1700** of FIG. **17A** and top-view **1706** of FIG. **17B**, in some embodiments, an active area **802** is defined within the stacked substrate **102** after depositing the passivation layer **604**. The active area **802** is defined to contain the plurality of first source/drain contacts **104x** and the second source/drain contact **108**. In some embodiments, the active area **802** may be defined by selectively implanting ions **1702** into the stacked substrate **102** according to a third masking layer **1704**. The implanted ions damage the layers of the stacked substrate **102** to define an isolation region **804** that surrounds and defines the active area **802**. The damage to the layers prevents a 2 DEG from extending into the isolation region **804**. In some embodiments, the third masking layer **1704** may comprise a photosensitive material (e.g., photoresist).

[0083] As shown in cross-sectional view **1800** of FIG. **18A** and top-view **1808** of FIG. **18B**, the passivation layer **604** is selectively patterned to define openings **1802** extending through the passivation layer **604** and exposing the doped semiconductor material **602**. In some embodiments, the passivation layer **604** may be selectively patterned by exposing the passivation layer **604** to a third etchant **1806** according to a fourth masking layer **1804**. In some embodiments, the fourth masking layer **1804** may comprise a photosensitive material (e.g., photoresist). In various embodiments, the third etchant **1806** may comprise a wet etchant or a dry etchant.

[0084] As shown in cross-sectional view **1900** of FIG. **19A** and top-view **1904** of FIG. **19B**, a gate contact material **1902** is formed in the openings **1802** in the passivation layer **604** and over the fourth masking layer **1804**. In some embodiments, the gate contact material **1902** may comprise a metal such as aluminum, tungsten, cobalt, titanium, or the like. In some embodiments, the gate contact material **1902** may be formed by a deposition process (e.g., CVD, PVD, sputtering, PE-CVD, or the like) and/or a plating process (e.g., an electroplating process, an electro-less plating process, or the like). In some embodiments, a planarization process (e.g., a chemical mechanical planarization process) may be performed after forming the gate contact material **1902**.

[0085] As shown in cross-sectional view **2000** of FIG. **20A** and top-view **2002** of FIG. **20B**, the gate contact material (**1902** of FIGS. **19A-19B**) is patterned to define a gate contact **210**. The gate contact **210** and the doped semiconductor material **602** collectively define a plurality of gate structures **106x** that wrap around the plurality of first source/drain contacts **104x**. The second source/drain contact **108** wraps around the plurality of gate structures **106x**.

[0086] As shown in cross-sectional view **2100** of FIG. **21**, plurality of conductive contacts **126** are formed within an inter-level dielectric (ILD) layer **124** over the stacked substrate **102**. In some embodiments, the plurality of conductive contacts **126** may be formed by way of a damascene process. In such embodiments, an ILD layer **124** is formed over the stacked substrate **102**. The ILD layer **124** is etched to form contacts holes, which are subsequently filled with a conductive material (e.g., tungsten, copper, and/or aluminum). A chemical mechanical planarization (CMP) process is subsequently performed to remove excess of the conductive material from over the ILD layer **124**.

[0087] FIG. **22** illustrates a flow diagram of some embodiments of a method **2200** of forming an integrated chip having a HEMT device comprising gate structures wrapped around first source/drain contacts.

[0088] While the disclosed methods (e.g., methods **2200** and **3000**) are illustrated and described herein as a series of acts or events, it will be appreciated that the illustrated ordering of such acts or events are not to be interpreted in a limiting sense. For example, some acts may occur in different orders and/or concurrently with other acts or events apart from those illustrated and/or described herein. In addition, not all illustrated acts may be required to implement one or more aspects or embodiments of the description herein. Further, one or more of the acts depicted herein may be carried out in one or more separate acts and/or phases.

[0089] At **2202**, an epitaxial stack is formed over a base substrate. The epitaxial stack comprises an active layer over the base substrate, a barrier layer over the active layer, and a doped semiconductor

layer over the barrier layer. FIGS. **12A-12B** illustrate a cross-sectional view **1200** and a top-view **1206** of some embodiments corresponding to act **2202**.

[0090] At act **2204**, the doped semiconductor layer within the epitaxial stack is patterned to define cavities extending through a doped semiconductor material. FIGS. **13A-13B** illustrate a cross-sectional view **1300** and a top-view **1306** of some embodiments corresponding to act **2204**.

[0091] At act **2206**, a plurality of first source/drain contacts are formed over the epitaxial stack and within the cavities. FIGS. **14A-15B** illustrate cross-sectional views, **1400** and **1500**, and top-views, **1410** and **1502**, of some embodiments corresponding to act **2206**.

[0092] At act **2208**, a second source/drain contact is formed over the epitaxial stack and continuously surrounding the plurality of first source/drain contacts. FIGS. **14A-15B** illustrate cross-sectional views, **1400** and **1500**, and top-views, **1410** and **1502**, of some embodiments corresponding to act **2208**.

[0093] At act **2210**, a passivation layer is formed over the plurality of first source/drain contacts, the second source/drain contact, and the epitaxial stack. FIGS. **16A-16B** illustrate a cross-sectional view **1600** and a top-view **1602** of some embodiments corresponding to act **2210**.

[0094] At act **2212**, an active area is defined in the epitaxial stack, in some embodiments. The active area surrounds the plurality of first source/drain contacts, the second source/drain contact, and the doped semiconductor material. FIGS. **17A-17B** illustrate a cross-sectional view **1700** and a top-view **1706** of some embodiments corresponding to act **2212**.

[0095] At act **2214**, the passivation layer is patterned to define openings exposing the doped semiconductor material. FIGS. **18A-18B** illustrate a cross-sectional view **1800** and a top-view **1808** of some embodiments corresponding to act **2214**.

[0096] At act **2216**, a gate contact material is formed in the openings in the passivation layer. FIGS. **19A-19B** illustrate a cross-sectional view **1900** and a top-view **1904** of some embodiments corresponding to act **2216**.

[0097] At act **2218**, the gate contact material is patterned to define a plurality of gate structures that wrap around the plurality of first source/drain contacts. FIGS. **20A-20B** illustrate a cross-sectional view **2000** and a top-view **2002** of some embodiments corresponding to act **2218**.

[0098] At act **2220**, one or more conductive contacts are formed within an inter-level dielectric (ILD) layer formed over the epitaxial stack. FIG. **21** illustrates a cross-sectional view **2100** of some embodiments corresponding to act **2220**.

[0099] FIGS. **23A-29** illustrate some embodiments of a method of forming an integrated chip having a MISFET (metal-insulator-semiconductor field effect transistor) device comprising gate structures wrapped around first source/drain contacts. Although FIGS. **23A-29** are described in relation to a method, it will be appreciated that the structures disclosed in FIGS. **23A-29** are not limited to such a method, but instead may stand alone as structures independent of the method.

[0100] As shown in cross-sectional view **2300** of FIG. **23A** and top-view **2302** of FIG. **23B**, an epitaxial stack **1202** is formed over a base substrate **116** to define a stacked substrate **102**. In some embodiments, the epitaxial stack **1202** may comprise an active layer **120** formed over the base substrate **116** and a barrier layer **122** formed on the active layer **120**. In some embodiments, the epitaxial stack **1202** may also comprise a buffer layer **118** formed onto the base substrate **116** prior to the formation of the active layer **120**.

[0101] As shown in cross-sectional view **2400** of FIG. **24A** and top-view **2406** of FIG. **24B**, the epitaxial stack **1202** may be selectively patterned according to a first masking layer **2402** to form a plurality of first source/drain recesses **1404** and a second source/drain recess **1406**. In some embodiments, the plurality of first source/drain recesses **1404** and the second source/drain recess **1406** may extend through the barrier layer **122** and into the active layer **120**. In some embodiments, the epitaxial stack **1202** may be selectively patterned by exposing the epitaxial stack **1202** to a first etchant **2404** according to the first masking layer **2402**. In some embodiments, the first masking layer **2402** may comprise a photosensitive material (e.g., photoresist). In various embodiments, the

first etchant **2404** may comprise a wet etchant or a dry etchant.

[0102] As shown in cross-sectional view **2500** of FIG. 25A and top-view **2502** of FIG. 25B, a conductive material is formed within the plurality of first source/drain recesses **1404** and the second source/drain recess **1406** to define a plurality of first source/drain contacts **104x** and a second source/drain contact **108**. In various embodiments, the conductive material may comprise a metal, such as aluminum, tungsten, titanium, cobalt, or the like. In some alternative embodiments (not shown), the plurality of first source/drain contacts **104x** and the second source/drain contact **108** may be formed over the barrier layer **122** without forming the one or more source contact recesses and the drain contact recess.

[0103] As shown in cross-sectional view **2600** of FIG. 26A and top-view **2604** of FIG. 26B, an active area **802** is defined within the stacked substrate **102**, in some embodiments. In some embodiments, the active area **802** may be defined by selectively implanting ions **1702** into the stacked substrate **102** according to a second masking layer **2602**. The implanted ions damage the layers of the stacked substrate **102** to define an isolation region **804** that surrounds and defines the active area **802**. The damage to the layers prevents a 2 DEG from extending into the isolation region **804**. In some embodiments, the second masking layer **2602** may comprise a photosensitive material (e.g., photoresist).

[0104] As shown in cross-sectional view **2700** of FIG. 27A and top-view **2704** of FIG. 27B, a gate dielectric layer **2702** and a gate contact material **1902** are formed over the stacked substrate **102**. In various embodiments, the gate dielectric layer **2702** may comprise an oxide (e.g., silicon dioxide), a nitride (e.g., silicon nitride), or the like. In various embodiments, the gate contact material **1902** may comprise doped polysilicon, a metal (e.g., aluminum, titanium, cobalt, tungsten, or the like), or the like. In some embodiments, the gate dielectric layer **2702** may be formed by deposition processes (e.g., CVD, PVD, sputtering, PE-CVD, or the like). In some embodiments, the gate contact material **1902** may be formed by deposition processes (e.g., CVD, PVD, sputtering, PE-CVD, or the like) and/or a plating process (e.g., an electroplating process, an electro-less plating process, or the like).

[0105] As shown in cross-sectional view **2800** of FIG. 28A and top-view **2806** of FIG. 28B, the gate dielectric layer (**2702** of FIG. 27A) and the gate contact material (**1902** of FIG. 27A) are selectively patterned to define a plurality of gate structures **106x** that wrap around the plurality of first source/drain contacts **104x**. The plurality of gate structures **106x** respectively comprise an insulating material **702** and a gate contact **210** over the insulating material **702**. In some embodiments, the gate dielectric layer (**2702** of FIG. 27A) and the gate contact material (**1902** of FIG. 27A) may be selectively patterned by exposing the gate dielectric layer and the gate contact material to a second etchant **2804** according to a third masking layer **2802**. In some embodiments, the third masking layer **2802** may comprise a photosensitive material (e.g., photoresist). In various embodiments, the second etchant **2804** may comprise a wet etchant or a dry etchant.

[0106] As shown in cross-sectional view **2900** of FIG. 29, a plurality of conductive contacts **126** are formed within an inter-level dielectric (ILD) layer **124** formed over the stacked substrate **102**. In some embodiments, the plurality of conductive contacts **126** may respectively be formed by way of a damascene process.

[0107] FIG. 30 illustrates a flow diagram of some embodiments of a method **3000** of forming an integrated chip having a MISFET device comprising gate structures wrapped around first source/drain contacts.

[0108] At act **3002**, an epitaxial stack is formed over a substrate. The epitaxial stack comprises an active layer and a barrier layer over the active layer. FIGS. 23A-23B illustrate a cross-sectional view **2300** and a top-view **2302** of some embodiments corresponding to act **3002**.

[0109] At act **3004**, a plurality of first source/drain contacts are formed over the epitaxial stack. FIGS. 24A-25B illustrate cross-sectional views, **2400** and **2500**, and top-views, **2406** and **2502**, of some embodiments corresponding to act **3004**.

[0110] At act **3006**, a second source/drain contact is formed over the epitaxial stack and surrounding the plurality of first source/drain contacts. FIGS. **24A-25B** illustrate cross-sectional views, **2400** and **2500**, and top-views, **2406** and **2502**, of some embodiments corresponding to act **3006**.

[0111] At act **3008**, an active area is defined in the epitaxial stack and surrounding the plurality of first source/drain contacts and the second source/drain contact. FIGS. **26A-26B** illustrate a cross-sectional view **2600** and a top-view **2604** of some embodiments corresponding to act **3008**.

[0112] At act **3010**, a gate dielectric layer is formed over the epitaxial stack. FIGS. **27A-27B** illustrate a cross-sectional view **2700** and a top-view **2704** of some embodiments corresponding to act **3010**.

[0113] At act **3012**, a gate contact material is formed over the gate dielectric. FIGS. **27A-27B** illustrate a cross-sectional view **2700** and a top-view **2704** of some embodiments corresponding to act **3012**.

[0114] At act **3014**, the gate contact material and the gate dielectric layer are patterned to define a plurality of gate structures that wrap around the plurality of first source/drain contacts. FIGS. **28A-28B** illustrate a cross-sectional view **2800** and a top-view **2806** of some embodiments corresponding to act **3014**.

[0115] At act **3016**, one or more conductive contacts are formed within an inter-level dielectric (ILD) layer formed over the epitaxial stack. FIG. **29** illustrates a cross-sectional view **2900** of some embodiments corresponding to act **3016**.

[0116] Accordingly, in some embodiments, the present disclosure relates to a high-voltage transistor device comprising a gate structure that is configured to provide for improved isolation between source/drain contacts. The gate structure wraps around a first source/drain contact and a second source/drain contact that wraps around the gate structure. Because the gate structure is able to disrupt an underlying two-dimensional electron gas (2 DEG) within the substrate, having the gate structure wrap around the first source/drain contact disrupts the 2 DEG along a closed and unbroken path surrounding the first source/drain contact.

[0117] In some embodiments, the present disclosure relates to a transistor device. The transistor device includes a plurality of first source/drain contacts disposed over a substrate; a plurality of gate structures disposed over the substrate between the plurality of first source/drain contacts, the plurality of gate structures wrapping around the plurality of first source/drain contacts in a plurality of closed loops; and a second source/drain contact disposed over the substrate between the plurality of gate structures, the second source/drain contact continuously wrapping around the plurality of gate structures as a continuous structure. In some embodiments, the second source/drain contact includes a plurality of loops having interior sidewalls defining a plurality of openings that respectively surround one of the plurality of first source/drain contacts and one of the plurality of gate structures. In some embodiments, the second source/drain contact includes a plurality of loops respectively defined by a curved sidewall of the second source/drain contact. In some embodiments, the transistor device further includes an isolation region disposed within the substrate and defining an active area, the plurality of first source/drain contacts, the plurality of gate structures, and the second source/drain contact disposed directly over the active area. In some embodiments, the plurality of first source/drain contacts are separated along a first direction; and the active area has a first width and a second width larger than the first width, the first width and the second width measured along a second direction that is perpendicular to the first direction. In some embodiments, the plurality of gate structures are separated along a first direction; and the second source/drain contact continuously extends in the first direction past outermost ones of the plurality of gate structures. In some embodiments, the plurality of first source/drain contacts are source contacts and the second source/drain contact is a drain contact. In some embodiments, the plurality of gate structures include a first gate structure that wraps around a first source/drain contact of the plurality of first source/drain contacts; and the first gate structure continuously

extends between a first end disposed along a first side of the first source/drain contact and a second end disposed along the first side of the first source/drain contact, the first end separated from the second end by a non-zero distance. In some embodiments, the substrate includes an active layer disposed over a base substrate; a barrier layer disposed over the active layer, a two-dimensional electron gas (2 DEG) being present at an interface of the active layer and the barrier layer; and the plurality of gate structures are configured to disrupt the 2 DEG along a plurality of closed paths extending around the plurality of first source/drain contacts. In some embodiments, the second source/drain contact includes a first closed loop surrounding a first gate structure of the plurality of gate structures and a second loop surrounding a second gate structure of the plurality of gate structures; and the second loop does not extend completely around the second gate structure.

[0118] In other embodiments, the present disclosure relates to an integrated chip. The integrated chip includes a substrate having an active layer and a barrier layer over the active layer; a plurality of first source/drain contacts disposed over the active layer and separated along a first direction; a plurality of gate structures disposed over the active layer and extending around the plurality of first source/drain contacts along continuous and unbroken paths; and a second source/drain contact that is separated from the plurality of first source/drain contacts by the plurality of gate structures. In some embodiments, the plurality of gate structures include interior sidewalls defining a plurality of openings that extend through the plurality of gate structures and that surround the plurality of first source/drain contacts in closed loops. In some embodiments, the second source/drain contact extends as a continuous structure around the plurality of gate structures. In some embodiments, the second source/drain contact includes a first loop extending completely around a first gate structure of the plurality of gate structures and a second loop that extends part way, but not entirely, around a second gate structure of the plurality of gate structures. In some embodiments, the integrated chip further includes an isolation region disposed within the substrate and defining an active area, the active area having curved edges that are conformal to curved sidewalls of the second source/drain contact. In some embodiments, the active area has a length along the first direction and a width along a second direction that is perpendicular to the first direction, the length larger than the width. In some embodiments, the integrated chip further includes a field plate arranged between the second source/drain contact and a first source/drain contact of the plurality of first source/drain contacts, the field plate extending in a closed loop surrounding the first source/drain contact. In some embodiments, the second source/drain contact includes interior sidewalls defining a plurality of openings extending through the second source/drain contact, the plurality of openings disposed in a first row extending along the first direction and in a second row extending along the first direction and separated from the first row along a second direction that is perpendicular to the first direction.

[0119] In yet other embodiments, the present disclosure relates to a method of forming a transistor device. The method includes forming a plurality of first source/drain contacts over a stacked substrate; forming a second source/drain contact over the stacked substrate, the second source/drain contact continuously wrapping around the plurality of first source/drain contacts; and forming a plurality of gate structures over the stacked substrate, the plurality of gate structures laterally between the plurality of first source/drain contacts and the second source/drain contact. In some embodiments, the plurality of gate structures wrap around the plurality of first source/drain contacts along a plurality of continuous and unbroken paths; and the second source/drain contact wraps around the plurality of gate structures along a continuous and unbroken path.

[0120] The foregoing outlines features of several embodiments so that those skilled in the art may better understand the aspects of the present disclosure. Those skilled in the art should appreciate that they may readily use the present disclosure as a basis for designing or modifying other processes and structures for carrying out the same purposes and/or achieving the same advantages of the embodiments introduced herein. Those skilled in the art should also realize that such equivalent constructions do not depart from the spirit and scope of the present disclosure, and that

they may make various changes, substitutions, and alterations herein without departing from the spirit and scope of the present disclosure.

Claims

1. A method, comprising: forming a plurality of first source/drain contacts over a substrate; forming a second source/drain contact over the substrate, wherein the second source/drain contact wraps around the plurality of first source/drain contacts; forming a plurality of gate structures over the substrate, wherein the plurality of gate structures are laterally between the plurality of first source/drain contacts and the second source/drain contact; and forming an isolation region within the substrate, wherein the isolation region has one or more curved edges that face a curved outermost sidewall of the second source/drain contact, the one or more curved edges being separated from the curved outermost sidewall by a non-zero distance.
2. The method of claim 1, wherein the plurality of first source/drain contacts have a first straight sidewall and the second source/drain contact has a second straight sidewall that extends past opposing ends of the first straight sidewall.
3. The method of claim 1, wherein the isolation region is entirely outside of the second source/drain contact.
4. The method of claim 1, wherein the isolation region comprises a semiconductor material of the substrate having a damaged crystalline lattice.
5. The method of claim 1, wherein an edge of the isolation region is conformal to an outer edge of the second source/drain contact.
6. The method of claim 1, wherein the plurality of first source/drain contacts respectively have a greater width than the plurality of gate structures.
7. The method of claim 1, wherein the isolation region surrounds an active region that oscillates between a maximum width and a minimum width measured along a direction extending along a long axis of one of the plurality of first source/drain contacts.
8. The method of claim 1, wherein the isolation region has a straight edge that extends past opposing ends of the one of the plurality of first source/drain contacts.
9. A method, comprising: forming a plurality of first source/drain contacts over a substrate; forming a second source/drain contact over the substrate, wherein the second source/drain contact encloses the plurality of first source/drain contacts; forming a plurality of gate structures over the substrate, wherein the plurality of gate structures are laterally between the plurality of first source/drain contacts and the second source/drain contact; and wherein the plurality of gate structures are separated from the plurality of first source/drain contacts by a first distance and are separated from the second source/drain contact by a second distance that is different than the first distance, the first distance and the second distance being measured along a direction that is perpendicular to long axes of the plurality of first source/drain contacts.
10. The method of claim 9, wherein ends of one of the plurality of first source/drain contacts are separated from a closest one of the plurality of gate structures by larger distances than sidewalls of the one of the plurality of first source/drain contacts.
11. The method of claim 9, wherein the plurality of first source/drain contacts comprise one or more curved outermost edges.
12. The method of claim 9, wherein the second source/drain contact is symmetric about a line that bisects one of the plurality of first source/drain contacts along a long axis of the one of the plurality of first source/drain contacts.
13. The method of claim 9, wherein the first distance is larger than the second distance.
14. The method of claim 9, wherein the second distance is larger than the first distance.
15. A method, comprising: a plurality of source contacts disposed over a substrate; a plurality of gate structures disposed over the substrate, wherein the plurality of gate structures wrap around one

or more of the plurality of source contacts in one or more closed loops; a drain contact disposed over the substrate, wherein the drain contact continuously wraps around one or more of the plurality of gate structures as a continuous structure; and wherein the plurality of gate structures comprise a bottom surface that is entirely contacting a topmost surface of the substrate.

16. The method of claim 15, wherein the plurality of gate structures respectively have a smaller height than the plurality of source contacts in a cross-sectional view.

17. The method of claim 15, wherein the plurality of gate structures respectively comprise a lower gate layer including a semiconductor material and a gate contact disposed on the lower gate layer.

18. The method of claim 17, wherein the lower gate layer comprises p-doped gallium nitride.

19. The method of claim 15, further comprising: forming an isolation region within the substrate, wherein an edge of the isolation region is conformal to an outer edge of the drain contact.

20. The method of claim 15, further comprising: forming an isolation region within the substrate, wherein the drain contact overlaps a part of the isolation region.
